

Six-Pack Trench IGBT

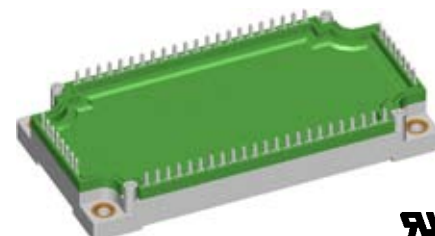
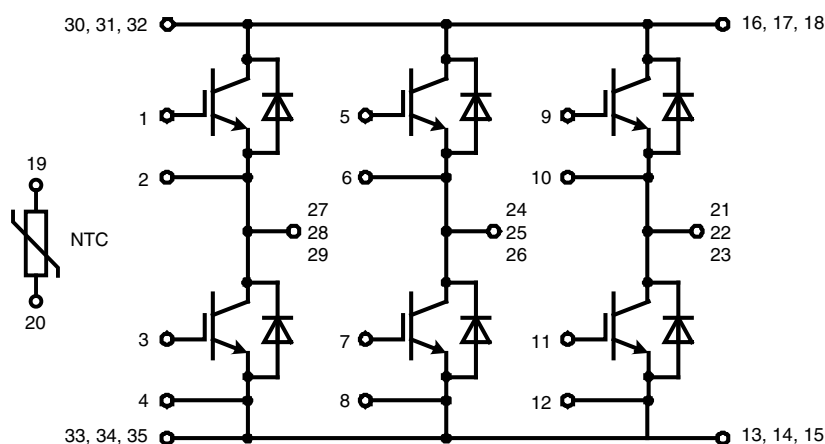
$$V_{CES} = 1200 \text{ V}$$

$$I_{C25} = 215 \text{ A}$$

$$V_{CE(sat)} = 1.7 \text{ V}$$

Part name (Marking on product)

MWI150-12T8T




E 72873

Pin configuration see outlines.

Features:

- Trench IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate

Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

Package:

- "E3-Pack" standard outline
- Insulated copper base plate
- Soldering pins for PCB mounting
- Temperature sense included

Output Inverter T1 - T6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
V_{GES}	max. DC gate voltage	continuous			± 20		V
V_{GEM}	max. transient collector gate voltage	transient			± 30		V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			215		A
I_{C80}		$T_C = 80^{\circ}\text{C}$			150		A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			690		W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 150\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.7 2.0	2.1		V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 6\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	5.0	5.8	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		6		mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500		nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		10770			pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 150\text{ A}$		860			nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 150\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 2.4\ \Omega$ $L_S = 70\text{ nH}$	$T_{VJ} = 125^{\circ}\text{C}$	270			ns
t_r	current rise time			50			ns
$t_{d(off)}$	turn-off delay time			500			ns
t_f	current fall time			340			ns
E_{on}	turn-on energy per pulse			15.5			mJ
E_{off}	turn-off energy per pulse			20			mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 2.4\ \Omega;$	$T_{VJ} = 125^{\circ}\text{C}$ $V_{CEK} = 1200\text{ V}$		300		A
SCSOA	short circuit safe operating area						
t_{SC}	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V};$	$T_{VJ} = 125^{\circ}\text{C}$		10		μs
I_{SC}	short circuit current	$R_G = 2.4\ \Omega;$ non-repetitive		600			A
R_{thJC}	thermal resistance junction to case	(per IGBT)			0.18		K/W

Output Inverter D1 - D6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			196		A
I_{F80}		$T_C = 80^{\circ}\text{C}$			132		A
V_F	forward voltage	$I_F = 150\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.95 1.85	2.2		V
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $di_F/dt = -2900\text{ A}/\mu\text{s}$ $I_F = 150\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	20			μC
I_{RM}	max. reverse recovery current			160			A
t_{rr}	reverse recovery time			320			ns
E_{rec}	reverse recovery energy			7			mJ
R_{thJC}	thermal resistance junction to case	(per diode)			0.28		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

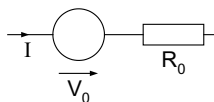
Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	Unit
R_{25}	resistance	$T_C = 25^\circ\text{C}$	4.75	5.0	5.25	k Ω
$B_{25/50}$				3375		K

Module

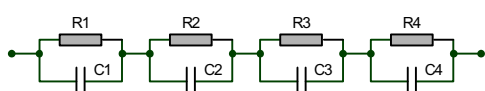
Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	Unit
T_{VJ}	operating temperature		-40		125	$^\circ\text{C}$
T_{VJM}	max. virtual junction temperature				150	$^\circ\text{C}$
T_{stg}	storage temperature		-40		125	$^\circ\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$			2500	V~
CTI	comparative tracking index				-	
M_d	mounting torque (M5)		2.7		3.3	Nm
d_s	creep distance on surface		10			mm
d_A	strike distance through air		7.5			mm
$R_{pin-chip}$	resistance pin to chip			2.5		m Ω
R_{thCH}	thermal resistance case to heatsink	with heatsink compound		0.02		K/W
Weight				300		g

0.0 Equivalent Circuits for Simulation



Ratings

Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_0	IGBT	T1 - T6		1.0		V
R_0				6.7		m Ω
V_0	Diode	D1 - D6		1.15		V
R_0				4.7		m Ω



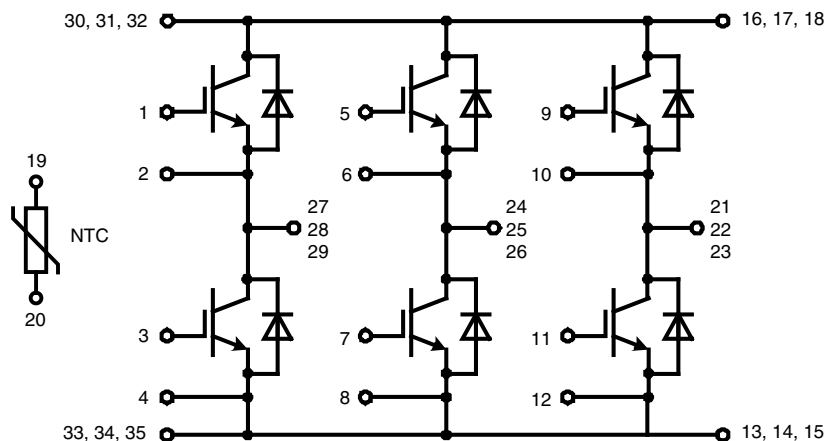
$$Z_{th}(t) = \sum_{i=1}^n \left[R_i \cdot \left(1 - \exp\left(-\frac{t}{\tau_i}\right) \right) \right]$$

$$\tau_i = R_i \cdot C_i$$

	IGBT	Diode
R_1	0.0267	0.054
R_2	0.0309	0.05
R_3	0.061	0.096
R_4	0.0614	0.08
τ_1	0.0025	0.0025
τ_2	0.076	0.076
τ_3	0.036	0.036
τ_4	0.076	0.076

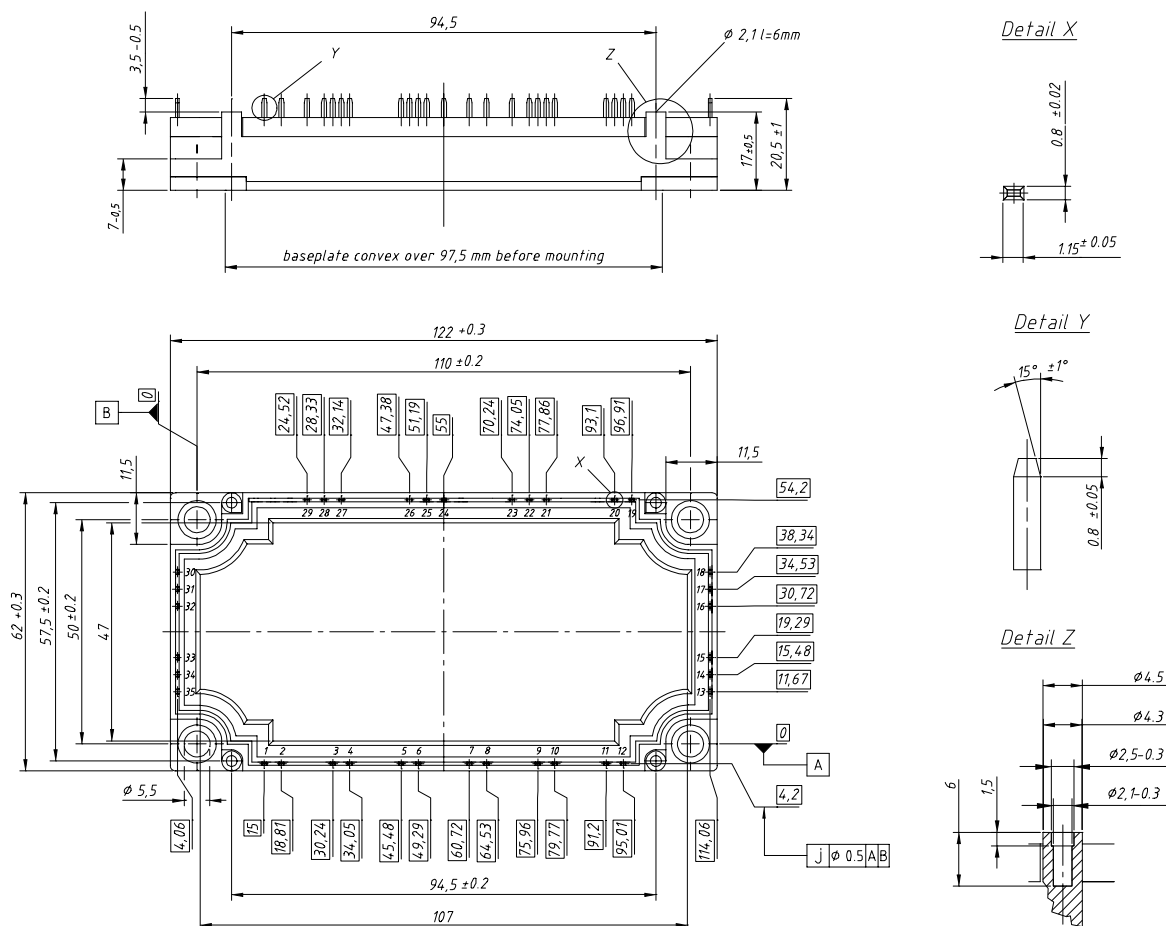
$T_C = 25^\circ\text{C}$ unless otherwise stated

Circuit Diagram



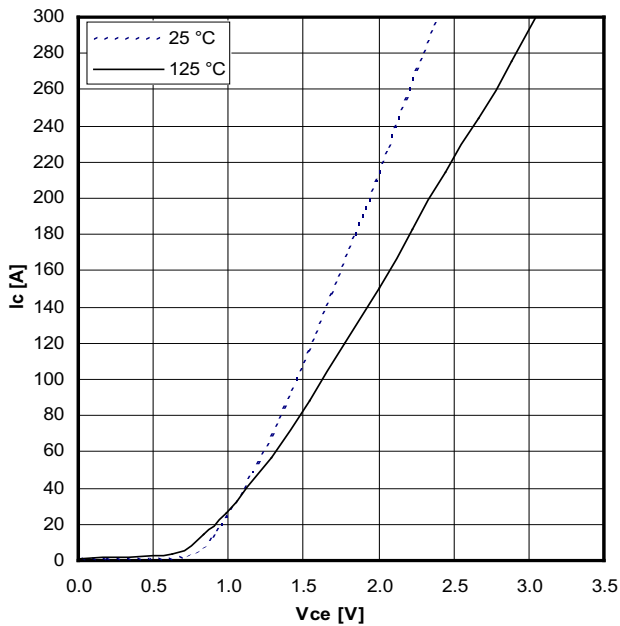
Outline Drawing

Dimensions in mm (1 mm = 0.0394")

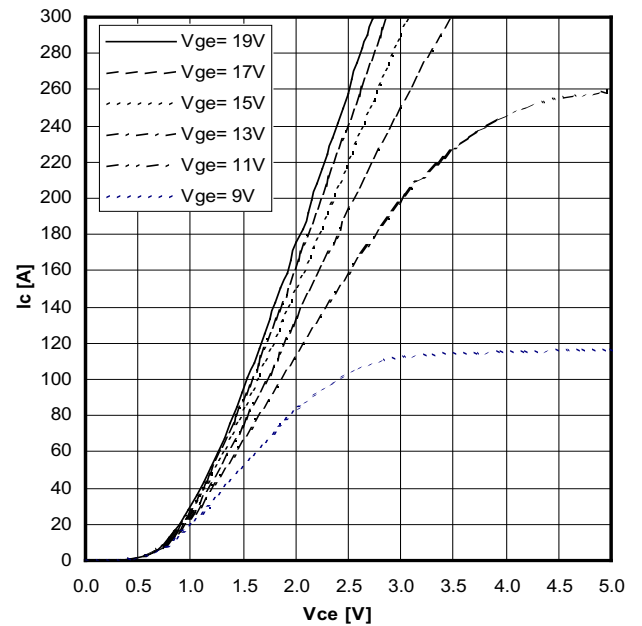


Product Marking

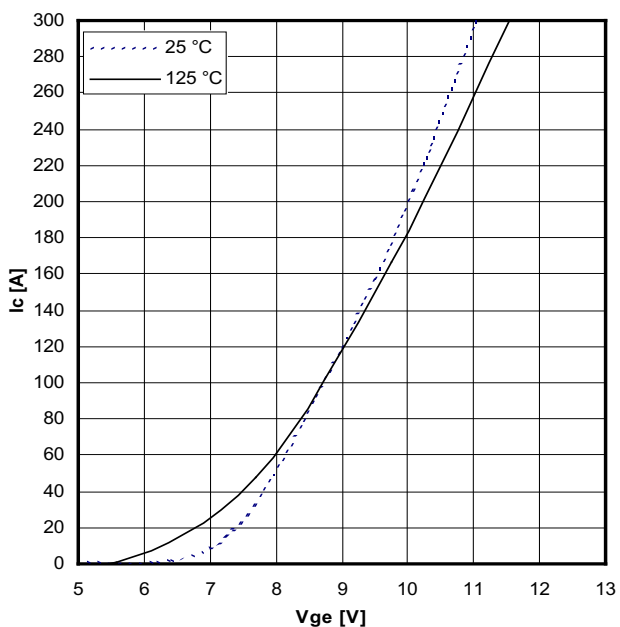
Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MWI150-12T8T	MWI150-12T8T	Box	5	502301

Inverter T1 - T6


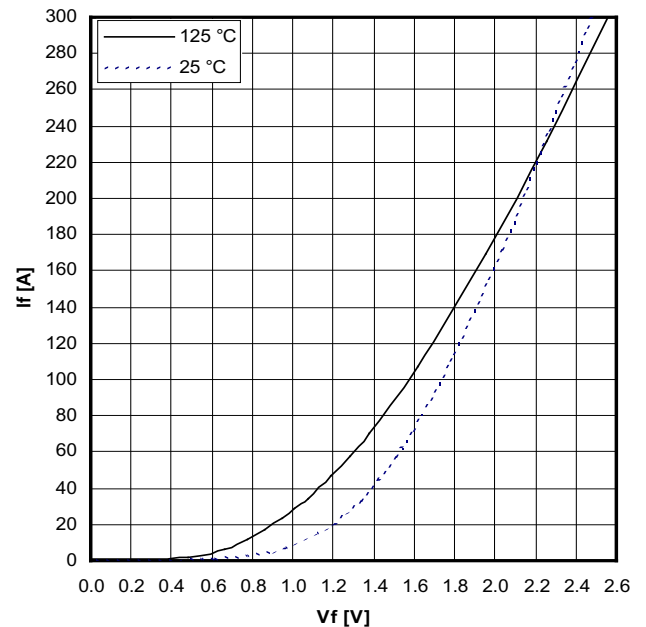
Typ. output characteristics



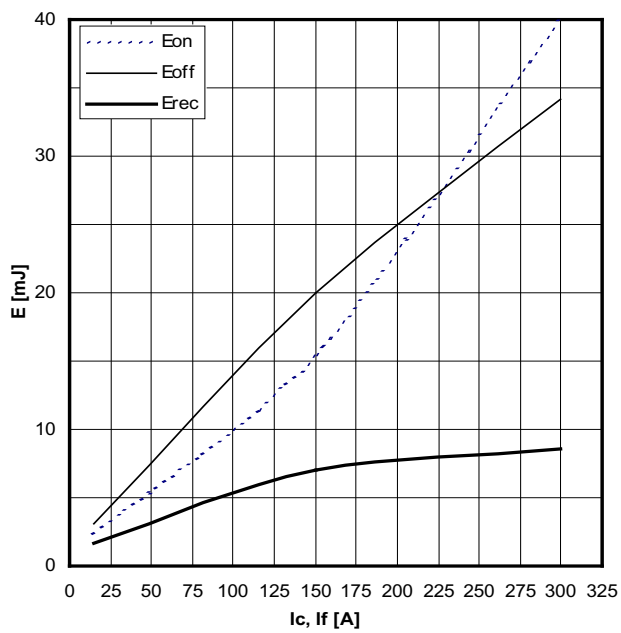
Typ. output characteristics



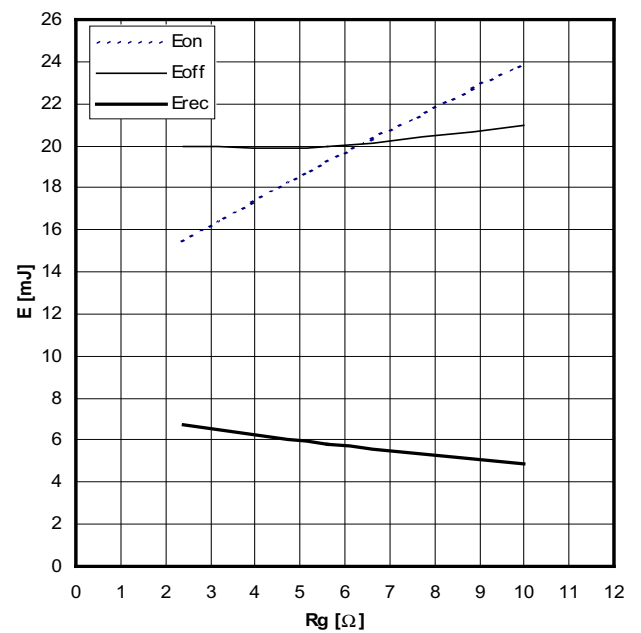
Typ. tranfer characteristics



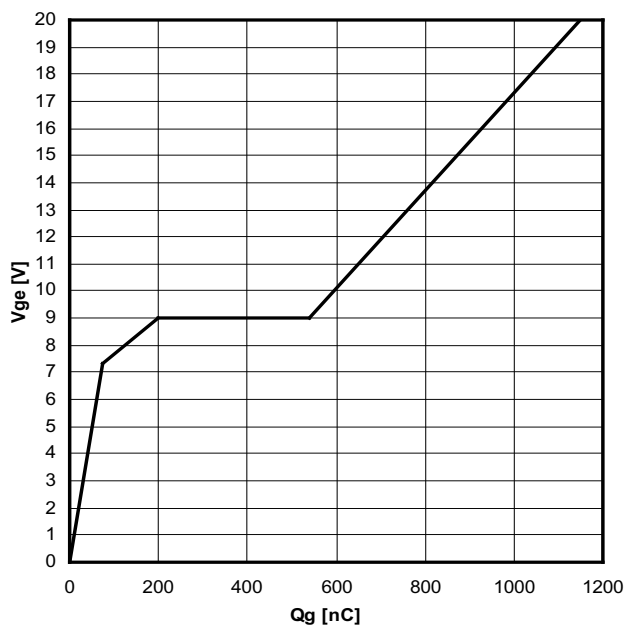
Typ. tranfer characteristics



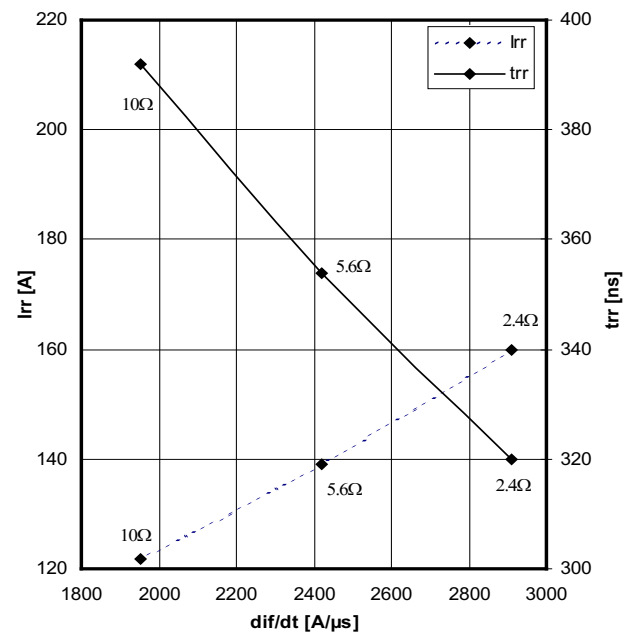
Typ. switching energy vs. collector current



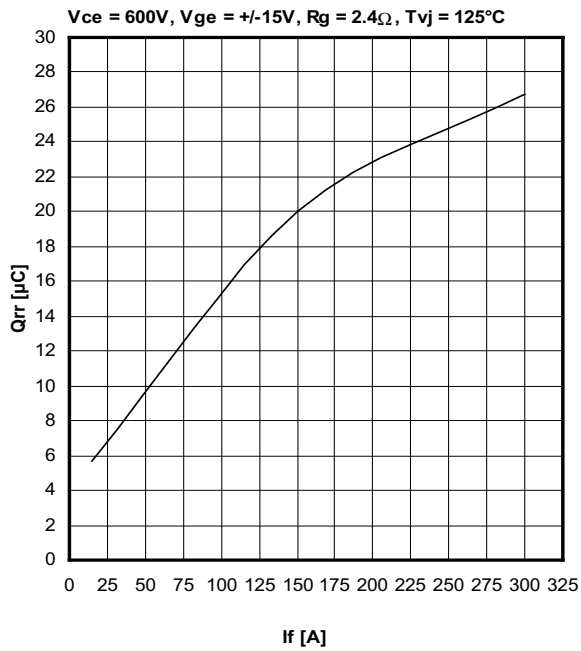
Typ. switching energy vs. gate resistance



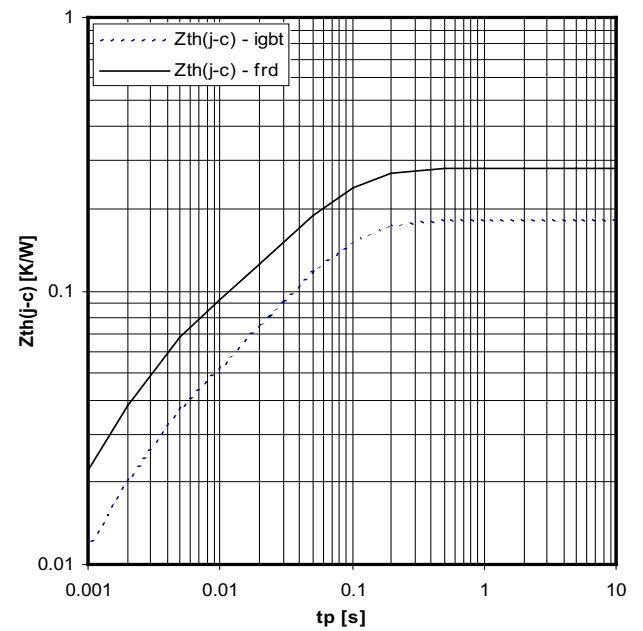
Typ. turn-on gate charge



Reverse recovery characteristics

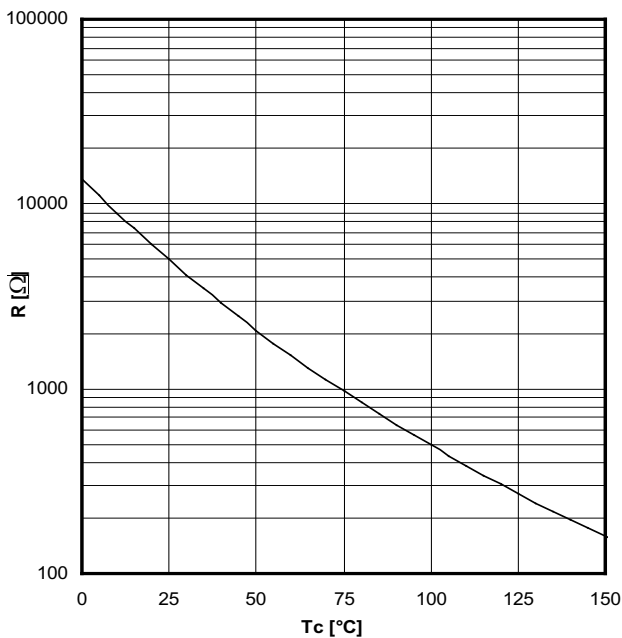


Reverse recovery characteristics



Typ. transient thermal impedance

NTC



Typ. NTC resistance versus temperature